MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

MMDT5401

Product specification

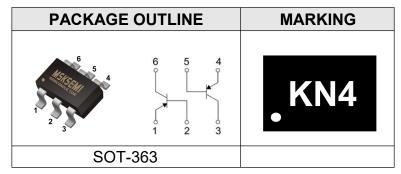




FEATURES

- Epitaxial Planar Die Construction
- Complementary NPN Type Available(MMDT 5551)
- Ideal for Medium Power Amplification and Switching

Reference News



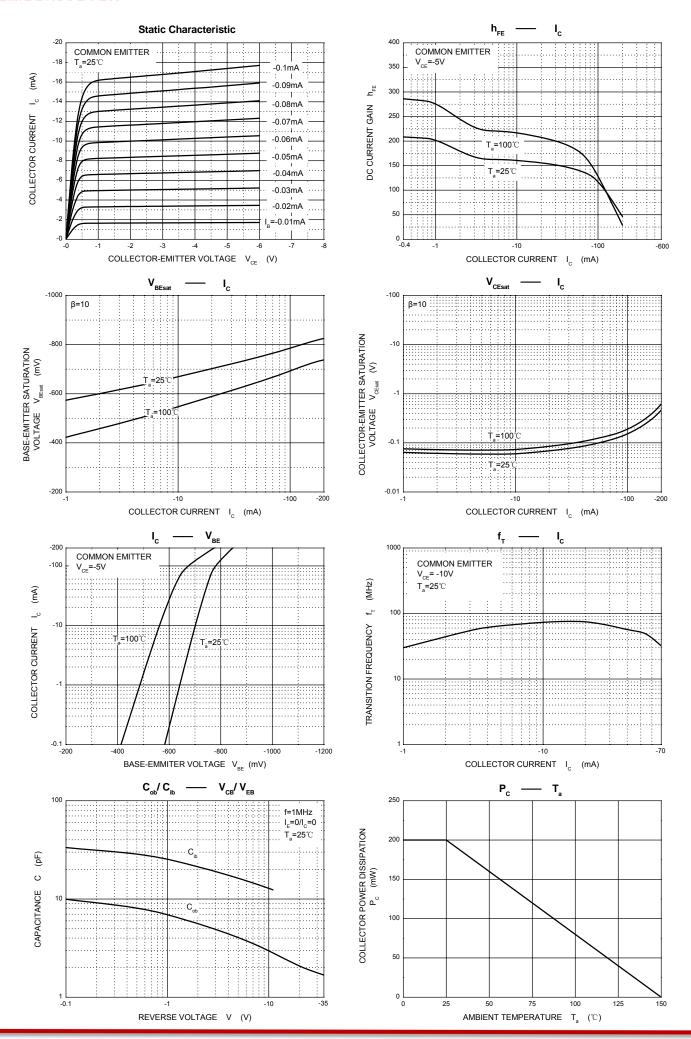
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V _{СВО}	Collector- Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-0.2	Α
Pc	Collector Power Dissipation	0.2	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

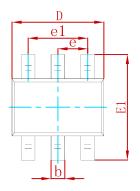
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _(BR) CBO	lc=-100μA , l _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	Ic= -1mA , I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l _E =-10μA, l _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-120 V , I _E =0			-0.05	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-3V , I _C =0			-0.05	μΑ
	h _{FE(1)}	V_{CE} =-5 V, I_{C} = -1mA	50			
DC current gain	h _{FE(2)}	V _{CE} =-5 V, I _C = -10mA	100		300	
	h _{FE(3)}	V _{CE} =-5 V, I _C = -50mA	50			
Collector emitter actuation valters	V _{CE(sat)1}	I _C =-10 mA, I _B =-1mA			-0.2	V
Collector-emitter saturation voltage	V _{CE(sat)2}	lc=-50 mA, l _B =-5mA			-0.5	V
Page emitter acturation valtage	V _{BE(sat)1}	I _C = -10 mA, I _B =-1mA			-1	V
Base-emitter saturation voltage	V _{BE(sat)2}	Ic= -50 mA, I _B =-5mA			-1	V
Transition frequency	f⊤	V _{CE} = -10V, I _C = -10mA,f = 100MHz	100			MHz
Output Capacitance	Cob	V _{CB} =-10V, I _E = 0,f=1MHz			6	pF
Noise Figure	NF	V _{CE} = -5.0V, I _C = -200μA,			8.0	dB
		$R_S = 10\Omega, f = 1.0kHz$				

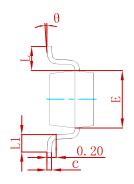


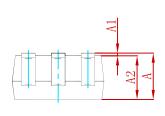




PACKAGEMECHANICALDATA

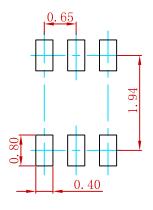






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650	TYP	0.026	TYP	
e1	1.200	1.400	0.047	0.055	
Ĺ	0.525 REF		0.021	I REF	
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMDT5401	SOT-363	3000



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